



**THE DATASHEET OF  
VMK90-02T2**

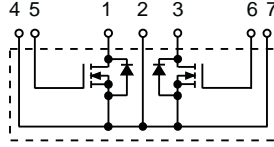


# Dual Power MOSFET Module

## VMK 90-02T2

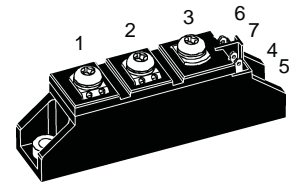
$V_{DSS} = 200 \text{ V}$   
 $I_{D25} = 83 \text{ A}$   
 $R_{DS(on)} = 25 \text{ m}\Omega$

Common-Source connected  
N-Channel Enhancement Mode



| Symbol        | Test Conditions   | Maximum Ratings     |                  |
|---------------|---|---------------------|------------------|
| $V_{DSS}$     | $T_J = 25^\circ\text{C to } 150^\circ\text{C}$                                  | 200                 | V                |
| $V_{DGR}$     | $T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GS} = 6.8 \text{ k}\Omega$    | 200                 | V                |
| $V_{GS}$      | Continuous  | $\pm 20$            | V                |
| $V_{GSM}$     | Transient   | $\pm 30$            | V                |
| $I_{D25}$     | $T_C = 25^\circ\text{C}$  | 83                  | A                |
| $I_{D80}$     | $T_C = 80^\circ\text{C}$  | 62                  | A                |
| $I_{DM}$      | $T_C = 25^\circ\text{C}, t_p = 10 \mu\text{s},$ pulse width limited by $T_{JM}$ | 330                 | A                |
| $P_D$         | $T_C = 25^\circ\text{C}, T_J = 150^\circ\text{C},$                              | 380                 | W                |
| $T_J$         |   | -40 ... +150        | $^\circ\text{C}$ |
| $T_{JM}$      |   | 150                 | $^\circ\text{C}$ |
| $T_{stg}$     |   | -40 ... +125        | $^\circ\text{C}$ |
| $V_{ISOL}$    | 50/60 Hz  | $t = 1 \text{ min}$ | 2500 V~          |
|               | $I_{ISOL} \leq 1 \text{ mA}$  | $t = 1 \text{ s}$   | 3000 V~          |
| $M_d$         | Mounting torque(M5 or 10-32 UNF)  | 2.5-4.0/22-35       | Nm/lb.in.        |
|               | Terminal connection torque (M5)   | 2.5-4.0/22-35       | Nm/lb.in.        |
| <b>Weight</b> | Typical including screws  | 90                  | g                |

TO-240 AA  
E 72873



1, 3 = Drain, 2 = Common Source  
5, 6 = Gate, 4, 7 = Kelvin Source

### Features

- Two MOSFET with common source
- International standard package JEDEC TO-240 AA
- Direct copper bonded  $\text{Al}_2\text{O}_3$  ceramic base plate
- Isolation voltage 3000 V~
- Low  $R_{DS(on)}$  HDMOST™ process
- Low package inductance for high speed switching
- Kelvin source contact
- Keyed twin plugs

### Applications

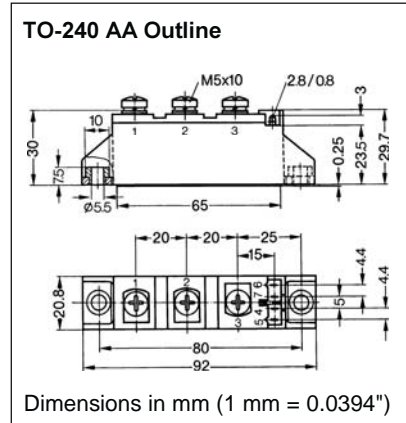
- Push-pull inverters
- Switched-mode and resonant-mode power supplies
- Uninterruptible power supplies (UPS)
- AC static switches

### Advantages

- Easy to mount with two screws
- Space and weight savings
- High power density
- Low losses

| Symbol       | Test Conditions   | Characteristic Values<br>( $T_J = 25^\circ\text{C}$ , unless otherwise specified) |      |                     |
|--------------|---|---|------|---------------------|
|              |   | min.  | typ. | max.                |
| $V_{DSS}$    | $V_{GS} = 0 \text{ V}, I_D = 1 \text{ mA}$  | 200   |      | V                   |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 3 \text{ mA}$   | 2   |      | V                   |
| $I_{GSS}$    | $V_{GS} = \pm 20 \text{ V DC}, V_{DS} = 0$  |   |      | 500 nA              |
| $I_{DSS}$    | $V_{DS} = 0.8 \cdot V_{DSS}, V_{GS} = 0 \text{ V}, T_J = 25^\circ\text{C}$<br>$V_{GS} = 0 \text{ V}, T_J = 125^\circ\text{C}$ |   |      | 400 $\mu\text{A}$   |
|              |   |   |      | 2 mA                |
| $R_{DS(on)}$ | $V_{GS} = 10 \text{ V}, I_D = 0.5 \cdot I_{D25}$<br>Pulse test, $t \leq 300 \mu\text{s}$ , duty cycle $d \leq 2\%$            |   |      | 25 $\text{m}\Omega$ |

| Symbol       | Test Conditions   | Characteristic Values<br>( $T_J = 25^\circ\text{C}$ , unless otherwise specified) |      |                |
|--------------|---|---|------|----------------|
|              |   | min.  | typ. | max.           |
| $g_{fs}$     | $V_{DS} = 10\text{ V}; I_D = 0.5 \cdot I_{D25}$ pulsed  |   | 60   | S              |
| $C_{iss}$    | $V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$   |   | 9000 | 15000 pF       |
| $C_{oss}$    |   |   | 1600 | 4500 pF        |
| $C_{rss}$    |   |   | 600  | 1500 pF        |
| $t_{d(on)}$  | $V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$<br>$R_G = 1\ \Omega$ (External), resistive load |   |      | 70 ns          |
| $t_r$        |   |   |      | 80 ns          |
| $t_{d(off)}$ |   |   |      | 200 ns         |
| $t_f$        |   |   |      | 100 ns         |
| $Q_g$        | $V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$   |   | 380  | 450 nC         |
| $Q_{gs}$     |   |   | 70   | 110 nC         |
| $Q_{gd}$     |   |   | 190  | 230 nC         |
| $R_{thJC}$   |   |   |      | 0.33 K/W       |
| $R_{thJK}$   | with heat transfer paste  |   |      | 0.53 K/W       |
| $d_s$        | Creepage distance on surface  | 12.7  |      | mm             |
| $d_A$        | Strike distance through air   | 9.6   |      | mm             |
| $a$          | Max. allowable acceleration   | 50  |      | $\text{m/s}^2$ |



| Symbol   | Test Conditions   | Characteristic Values<br>( $T_J = 25^\circ\text{C}$ , unless otherwise specified) |      |        |
|----------|---|---|------|--------|
|          |   | min.  | typ. | max.   |
| $I_S$    | $V_{GS} = 0\text{ V}$   |   |      | 83 A   |
| $I_{SM}$ | Repetitive; pulse width limited by $T_{JM}$   |   |      | 330 A  |
| $V_{SD}$ | $I_F = I_S; V_{GS} = 0\text{ V}$ ,<br>Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$ |   | 1.0  | 1.2 V  |
| $t_{rr}$ | $I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$            | 400   |      | 750 ns |

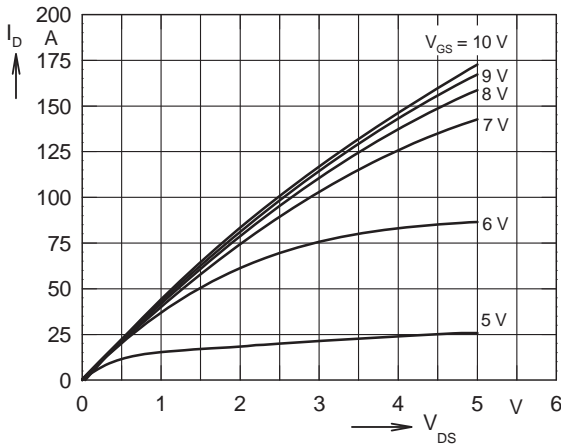


Fig. 1 Typical output characteristics  $I_D = f(V_{DS})$

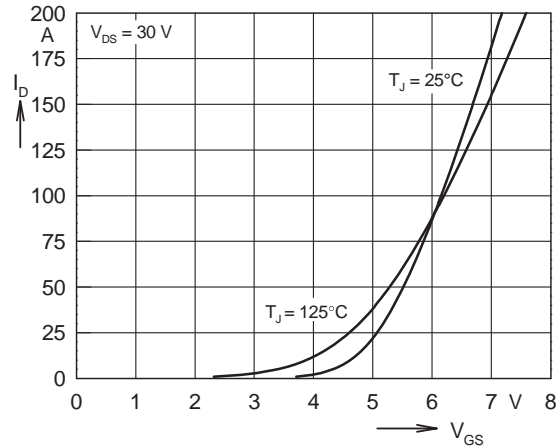


Fig. 2 Typical transfer characteristics  $I_D = f(V_{GS})$

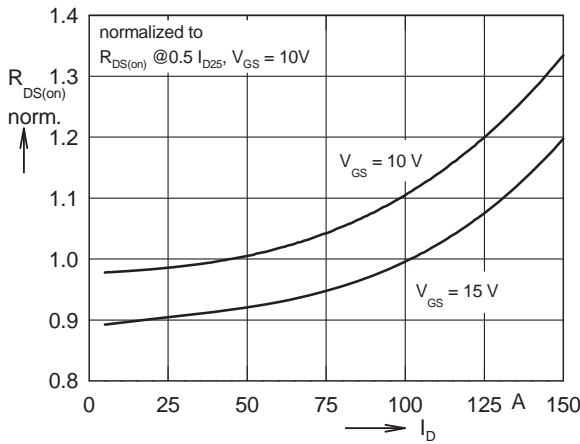


Fig. 3 Typical normalized  $R_{DS(on)} = f(I_D)$

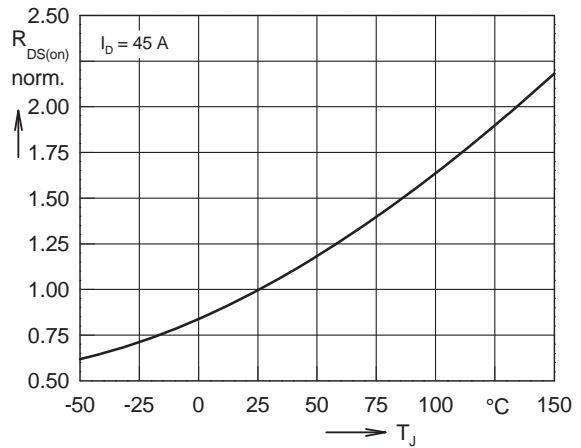


Fig. 4 Typical normalized  $R_{DS(on)} = f(T_J)$

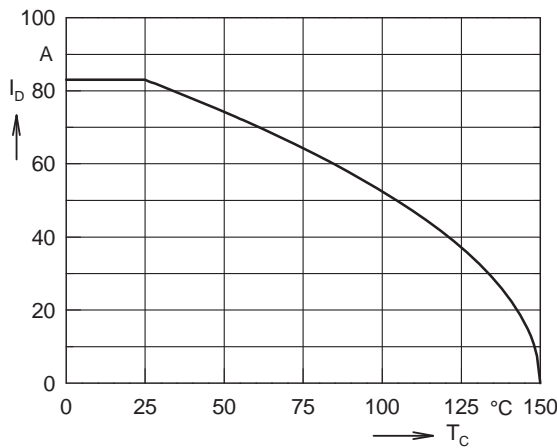


Fig. 5 Continuous drain current  $I_D = f(T_C)$

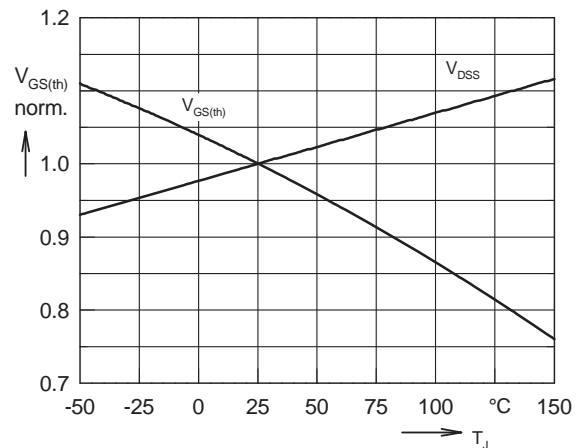


Fig. 6 Typical normalized  $V_{DS} = f(T_J)$ ,  $V_{GS(th)} = f(T_J)$

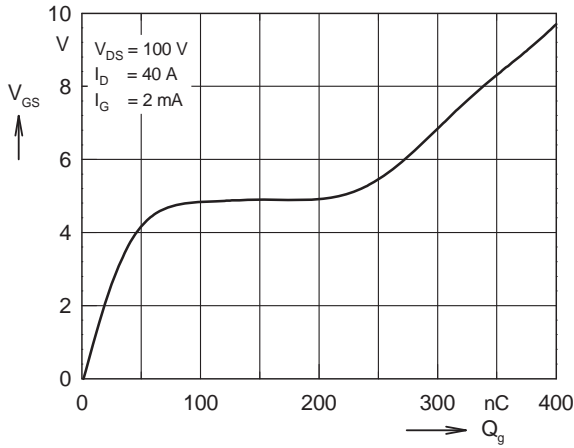


Fig. 7 Typical turn-on gate charge characteristics

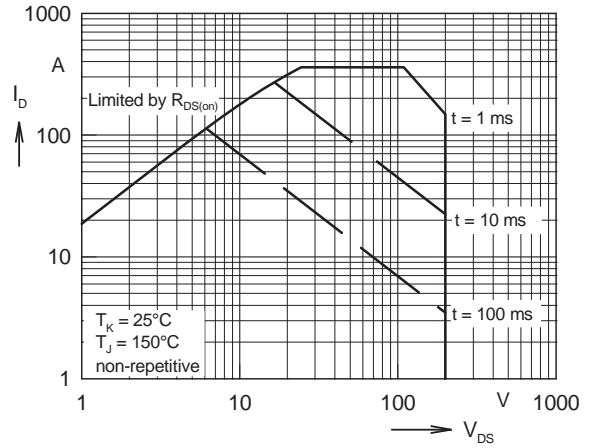


Fig. 8 Forward Safe Operating Area,  $I_D = f(V_{DS})$

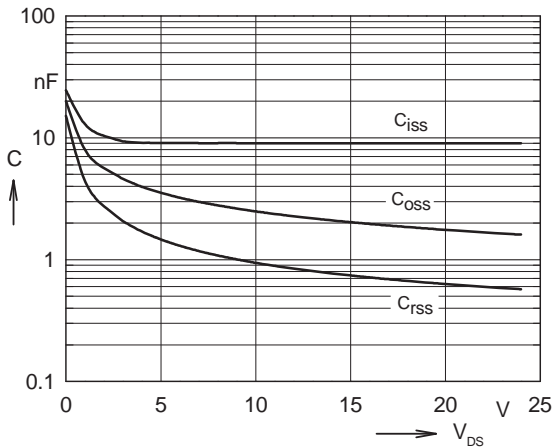


Fig. 9 Typical capacitances  $C = f(V_{DS})$ ,  $f = 1 \text{ MHz}$

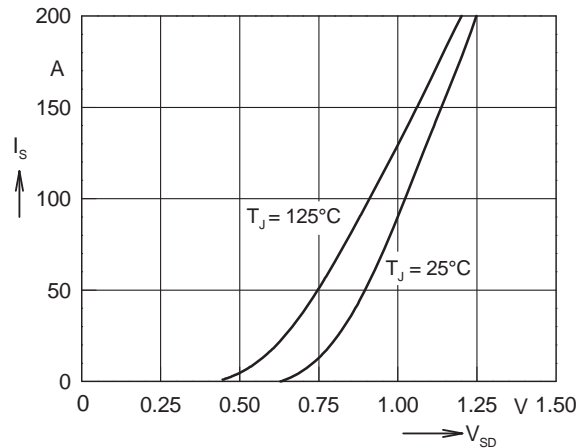


Fig. 10 Typical forward characteristics of reverse diode,  $I_S = f(V_{SD})$

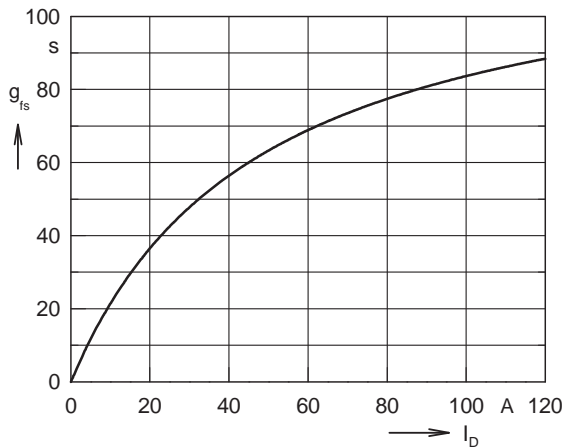


Fig. 11 Typical transconductance  $g_{is} = f(I_D)$

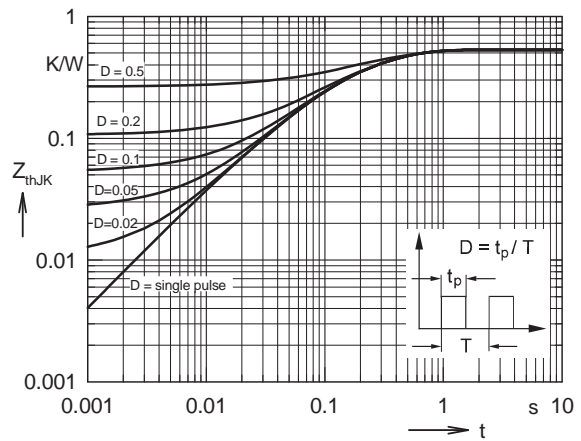


Fig. 12 Transient thermal resistance  $Z_{thJK} = f(t_p)$

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